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# 3SK290

Silicon N-Channel Dual Gate MOS FET

# HITACHI

ADE-208-271  
1st. Edition

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## Application

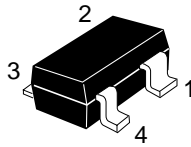
UHF RF amplifier

## Features

- Low noise figure.  
NF = 2.3 dB Typ. at f = 900 MHz
- High gain.  
PG = 19.3 dB Typ. at f = 900 MHz

## Outline

CMPAK-4



1. Source
2. Gate1
3. Gate2
4. Drain

**Absolute Maximum Ratings** ( $T_a = 25^{\circ}\text{C}$ )

<b>Item</b>	<b>Symbol</b>	<b>Ratings</b>	<b>Unit</b>
Drain to source voltage	$V_{DS}$	12	V
Gate 1 to source voltage	$V_{G1S}$	$\pm 8$	V
Gate 2 to source voltage	$V_{G2S}$	$\pm 8$	V
Drain current	$I_D$	25	mA
Channel power dissipation	Pch	100	mW
Channel temperature	Tch	125	$^{\circ}\text{C}$
Storage temperature	Tstg	-55 to +125	$^{\circ}\text{C}$

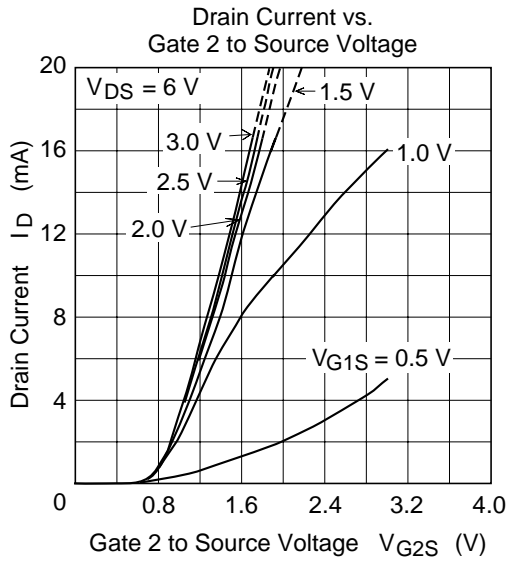
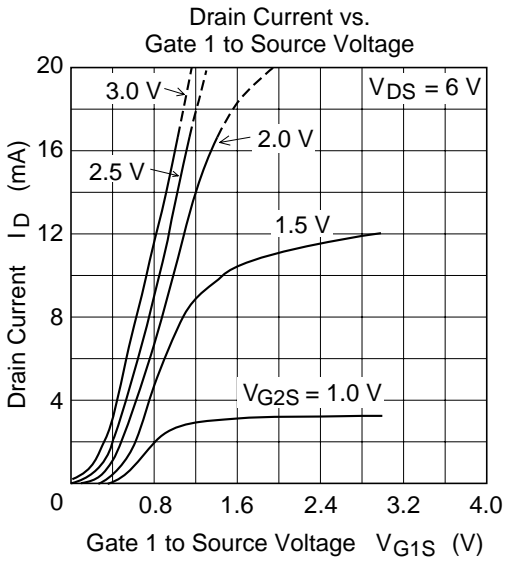
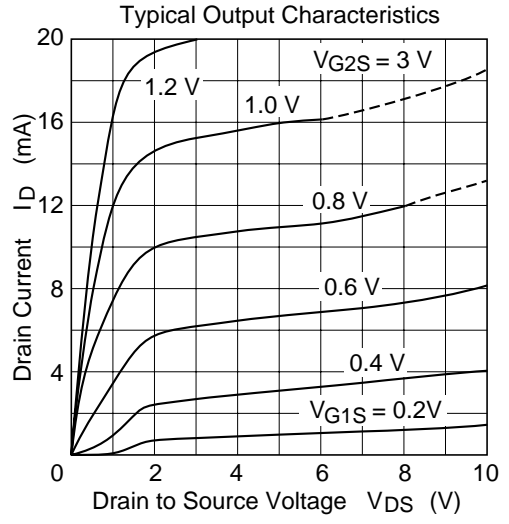
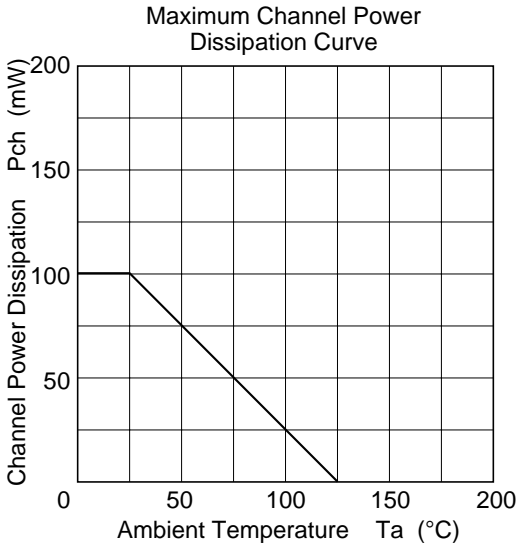
Attention: This device is very sensitive to electro static discharge.

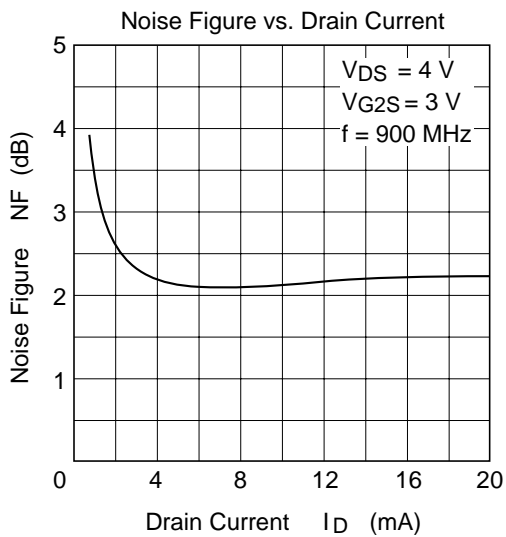
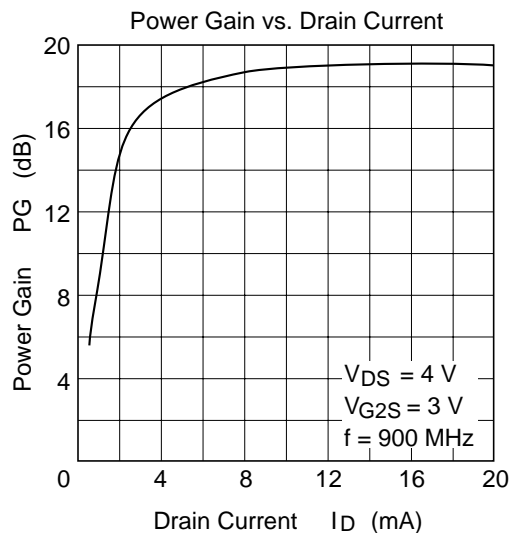
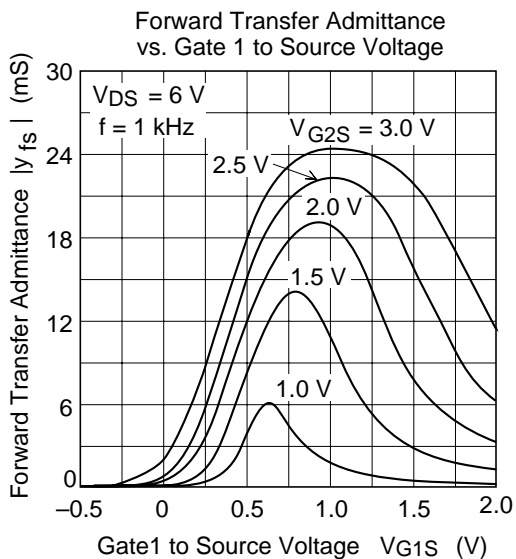
It is recommended to adopt appropriate cautions when handling this transistor.

## Electrical Characteristics (Ta = 25°C)

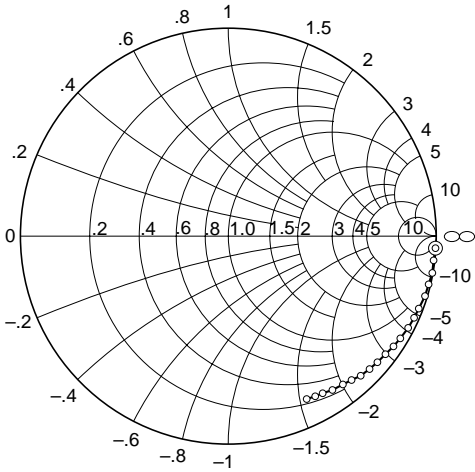
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSX}$	12	—	—	V	$I_D = 200 \mu A$ , $V_{G1S} = -3 V$ , $V_{G2S} = -3 V$
Gate 1 to source breakdown voltage	$V_{(BR)G1SS}$	$\pm 8$	—	—	V	$I_{G1} = \pm 10 \mu A$ , $V_{G2S} = V_{DS} = 0$
Gate 2 to source breakdown voltage	$V_{(BR)G2SS}$	$\pm 8$	—	—	V	$I_{G2} = \pm 10 \mu A$ , $V_{G1S} = V_{DS} = 0$
Gate 1 cutoff current	$I_{G1SS}$	—	—	$\pm 100$	nA	$V_{G1S} = \pm 6 V$ , $V_{G2S} = V_{DS} = 0$
Gate 2 cutoff current	$I_{G2SS}$	—	—	$\pm 100$	nA	$V_{G2S} = \pm 6 V$ , $V_{G1S} = V_{DS} = 0$
Drain current	$I_{DS(on)}$	0.5	—	10	mA	$V_{DS} = 6 V$ , $V_{G1S} = 0.5 V$ , $V_{G2S} = 3 V$
Gate 1 to source cutoff voltage	$V_{G1S(off)}$	-0.6	—	+0.5	V	$V_{DS} = 10 V$ , $V_{G2S} = 3 V$ , $I_D = 100 \mu A$
Gate 2 to source cutoff voltage	$V_{G2S(off)}$	0	—	+1.0	V	$V_{DS} = 10 V$ , $V_{G1S} = 3 V$ , $I_D = 100 \mu A$
Forward transfer admittance	$ y_{fs} $	16	22	—	mS	$V_{DS} = 6 V$ , $V_{G2S} = 3 V$ , $I_D = 10 mA$ , $f = 1 kHz$
Input capacitance	Ciss	1.2	1.8	2.2	pF	$V_{DS} = 6 V$ , $V_{G2S} = 3V$ , $I_D = 10 mA$ , $f = 1 MHz$
Output capacitance	Coss	0.7	1.2	1.4	pF	
Reverse transfer capacitance	Crss	—	0.02	0.03	pF	
Power gain	PG	17	19.3	—	dB	$V_{DS} = 4 V$ , $V_{G2S} = 3 V$ , $I_D = 10 mA$ , $f = 900 MHz$
Noise figure	NF	—	2.3	2.8	dB	

Note: Marking is "ZJ-".





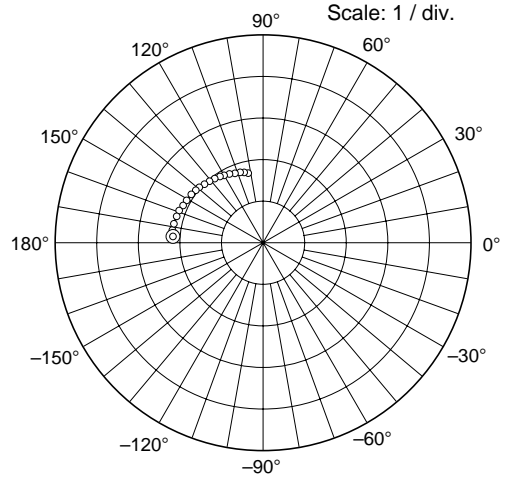
S11 Parameter vs. Frequency



Condition:  $V_{DS} = 4\text{ V}$ ,  $V_{GS} = 3\text{ V}$   
 $I_D = 10\text{ mA}$ ,  $Z_o = 50\ \Omega$   
 50 to 1000 MHz (50 MHz step)



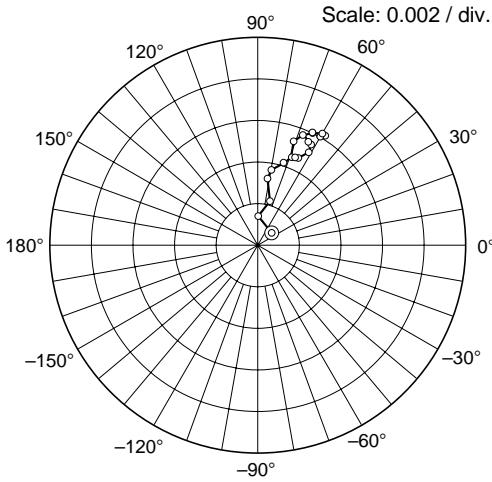
S21 Parameter vs. Frequency



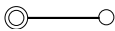
Condition:  $V_{DS} = 4\text{ V}$ ,  $V_{GS} = 3\text{ V}$   
 $I_D = 10\text{ mA}$ ,  $Z_o = 50\ \Omega$   
 50 to 1000 MHz (50 MHz step)



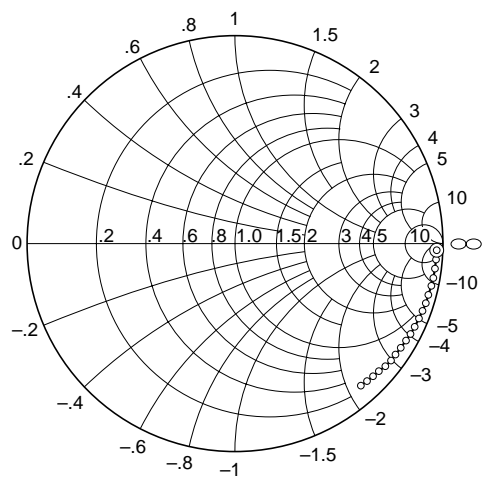
S12 Parameter vs. Frequency



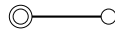
Condition:  $V_{DS} = 4\text{ V}$ ,  $V_{GS} = 3\text{ V}$   
 $I_D = 10\text{ mA}$ ,  $Z_o = 50\ \Omega$   
 50 to 1000 MHz (50 MHz step)



S22 Parameter vs. Frequency

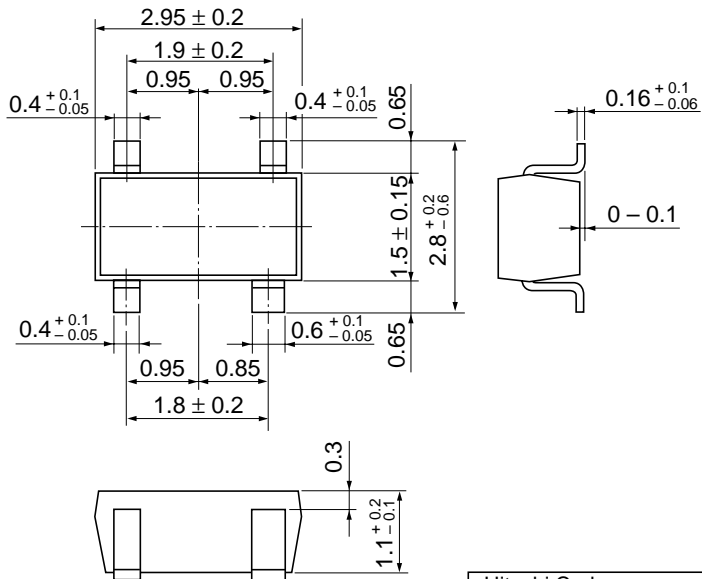


Condition:  $V_{DS} = 4\text{ V}$ ,  $V_{GS} = 3\text{ V}$   
 $I_D = 10\text{ mA}$ ,  $Z_o = 50\ \Omega$   
 50 to 1000 MHz (50 MHz step)



**S Parameter** ( $V_{DS} = 4 \text{ V}$ ,  $V_{G2S} = 3 \text{ V}$ ,  $I_D = 10 \text{ mA}$ ,  $Z_O = 50 \text{ } \Omega$ )

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
50	0.998	-3.3	2.17	176	0.001	41.3	0.971	-1.9
100	0.994	-6.7	2.20	172	0.001	88.9	0.971	-4.5
150	0.997	-10.2	2.19	168	0.002	74.4	0.970	-7.1
200	0.991	-13.5	2.17	163	0.003	81.6	0.969	-9.8
250	0.993	-16.9	2.16	159	0.004	79.7	0.967	-12.1
300	0.980	-20.8	2.12	155	0.004	72.6	0.965	-14.8
350	0.976	-23.7	2.10	151	0.005	66.9	0.962	-17.3
400	0.971	-27.0	2.08	146	0.005	70.9	0.959	-19.7
450	0.962	-30.7	2.05	142	0.006	67.7	0.956	-22.1
500	0.955	-33.7	2.03	139	0.006	63.9	0.953	-24.8
550	0.945	-36.9	1.99	135	0.006	64.1	0.950	-27.2
600	0.939	-40.2	1.96	131	0.006	63.9	0.946	-29.5
650	0.927	-43.3	1.93	127	0.006	59.9	0.942	-32.1
700	0.925	-46.5	1.90	123	0.006	60.0	0.939	-34.6
750	0.911	-49.4	1.87	120	0.006	58.3	0.933	-36.7
800	0.901	-52.3	1.84	116	0.006	60.3	0.930	-39.1
850	0.893	-55.9	1.81	112	0.005	62.0	0.925	-41.5
900	0.881	-59.0	1.78	108	0.005	61.2	0.921	-43.8
950	0.876	-61.5	1.75	105	0.005	65.0	0.917	-46.1
1000	0.869	-64.3	1.71	102	0.005	68.8	0.913	-48.4



Hitachi Code	MPAK-4
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.013 g



## Cautions

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# HITACHI

## Hitachi, Ltd.

Semiconductor & Integrated Circuits.  
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL      North America      : <http://semiconductor.hitachi.com/>  
             Europe                 : <http://www.hitachi-eu.com/hel/ecg>  
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## For further information write to:

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1> (408) 433-0223

Hitachi Europe GmbH  
Electronic components Group  
Dornacher Straße 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.  
16 Collyer Quay #20-00  
Hitachi Tower  
Singapore 049318  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia Ltd.  
Taipei Branch Office  
3F, Hung Kuo Building, No.167,  
Tun-Hwa North Road, Taipei (105)  
Tel: <886> (2) 2718-3666  
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower, World Finance Centre,  
Harbour City, Canton Road, Tsim Sha Tsui,  
Kowloon, Hong Kong  
Tel: <852> (2) 735 9218  
Fax: <852> (2) 730 0281  
Telex: 40815 HITEC HX

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